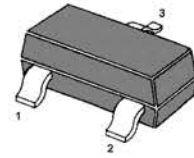
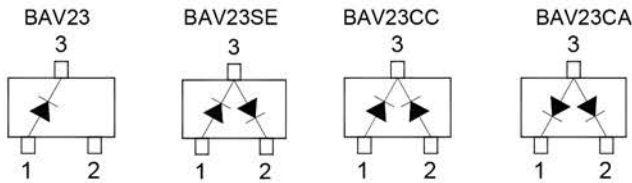


**Silicon Epitaxial Planar Diodes**

High voltage switching diode



BAV23 Marking Code: **HC**  
 BAV23SE Marking Code: **PY**  
 BAV23CC Marking Code: **PZ**  
 BAV23CA Marking Code: **RA**  
 SOT-23 Plastic Package

**Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )**

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	$V_{RRM}$	250	V
Reverse Voltage	$V_R$	200	V
Forward Current	$I_{F(AV)}$	400	mA
Repetitive Peak Forward Current	$I_{FRM}$	625	mA
Non-repetitive Peak Forward Surge Current	$I_{FSM}$	at $t = 10\text{ ms}$ 1.7	A
		at $t = 100\text{ }\mu\text{s}$ 3	
		at $t = 1\text{ }\mu\text{s}$ 9	
Power Dissipation	$P_{tot}$	350	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range	$T_j, T_{stg}$	- 65 to + 150	$^\circ\text{C}$

**Characteristics at  $T_a = 25\text{ }^\circ$** 

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	250	-	V
Forward Voltage at $I_F = 100\text{ mA}$ at $I_F = 200\text{ mA}$	$V_F$	-	1	V
		-	1.25	
Reverse Current at $V_R = 200\text{ V}, T_j = 25\text{ }^\circ\text{C}$ at $V_R = 200\text{ V}, T_j = 150\text{ }^\circ\text{C}$	$I_R$	-	100	nA
		-	100	$\mu\text{A}$
Total Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$	$C_{tot}$	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30\text{ mA}, I_{tr} = 0.1 \times I_R, R_L = 100\text{ }\Omega$	$t_{rr}$	-	50	ns

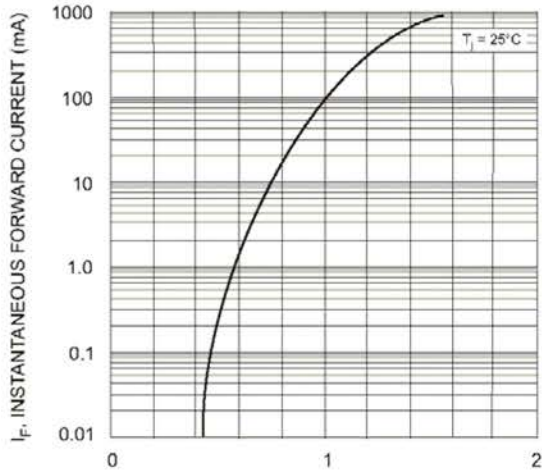


Fig. 1 Forward Characteristics

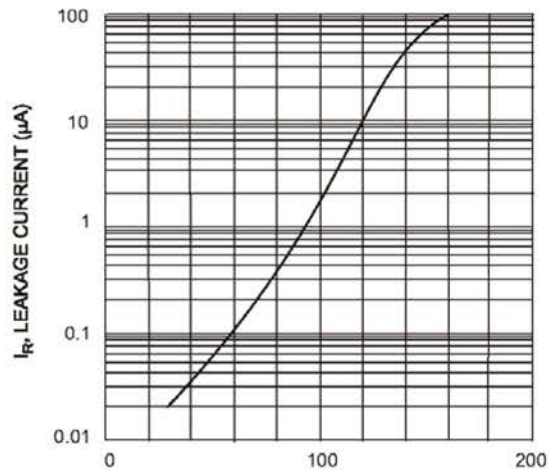


Fig. 2 Leakage Current vs Junction Temperature